

2SK3214

Silicon N Channel MOS FET
High Speed Power Switching

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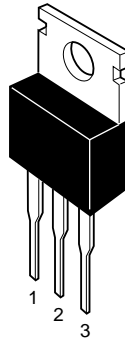
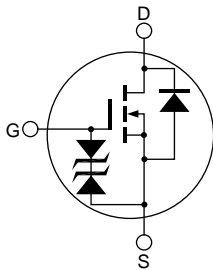
ADE-208-763(Z)
Target Specification
1st. Edition
December 1998

Features

- Low on-resistance
 $R_{DS} = 130m\Omega$ typ.
- High speed switching
- 4V gate drive device can be driven from 5V source

Outline

TO-220AB



1. Gate
2. Drain(Flange)
3. Source

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	200	V
Gate to source voltage	V_{GSS}	±20	V
Drain current	I_D	10	A
Drain peak current	$I_{D(pulse)}$ ^{Note1}	40	A
Body-drain diode reverse drain current	I_{DR}	10	A
Avalanche current	I_{AP} ^{Note3}	10	A
Avalanche energy	E_{AR} ^{Note3}	6.6	mJ
Channel dissipation	P_{ch} ^{Note2}	50	W
Channel temperature	T_{ch}	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

Note: 1. $PW \leq 10\mu s$, duty cycle $\leq 1\%$
 2. Value at $T_c = 25^\circ C$
 3. Value at $T_{ch} = 25^\circ C$, $R_g \geq 50\Omega$

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	200	—	—	V	$I_D = 10mA$, $V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20	—	—	V	$I_G = \pm 100\mu A$, $V_{DS} = 0$
Gate to source leak current	I_{GSS}	—	—	±10	μA	$V_{GS} = \pm 16V$, $V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	10	μA	$V_{DS} = 200V$, $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.0	—	2.5	V	$I_D = 1mA$, $V_{DS} = 10V$
Static drain to source on state resistance	$R_{DS(on)}$	—	130	170	mΩ	$I_D = 5A$, $V_{GS} = 10V$ ^{Note4}
	$R_{DS(on)}$	—	150	190	mΩ	$I_D = 5A$, $V_{GS} = 4V$ ^{Note4}
Forward transfer admittance	$ y_{fs} $	8	13	—	S	$I_D = 5A$, $V_{DS} = 10V$ ^{Note4}
Input capacitance	C_{iss}	—	1100	—	pF	$V_{DS} = 10V$
Output capacitance	C_{oss}	—	280	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	C_{rss}	—	130	—	pF	$f = 1MHz$
Turn-on delay time	$t_{d(on)}$	—	15	—	ns	$I_D = 5A$, $V_{GS} = 10V$
Rise time	t_r	—	75	—	ns	$R_L = 6\Omega$
Turn-off delay time	$t_{d(off)}$	—	280	—	ns	
Fall time	t_f	—	110	—	ns	
Body-drain diode forward voltage	V_{DF}	—	0.85	—	V	$I_F = 10A$, $V_{GS} = 0$
Body-drain diode reverse recovery time	t_{rr}	—	100	—	ns	$I_F = 10A$, $V_{GS} = 0$ $diF/dt = 50A/\mu s$

Note: 4. Pulse test

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